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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74ALVC16835

18-bit Universal Bus Driver with 3-state Outputs



ADE-205-192E (Z)
Preliminary
6th. Edition
January 1999

Description

The HD74ALVC16835 is an 18-bit universal bus driver designed for 2.3 V to 3.6 V V_{CC} operation.

Data flow from A to Y is controlled by output enable ($\overline{OE}$). The device operates in the transparent mode when the latch enable (LE) input is high. The A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A data is stored in the latch/flip flop on the low to high transition of the CLK. When $\overline{OE}$ is high, the outputs are in the high impedance state.

To ensure the high impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

Features

- Meets “PC SDRAM registered DIMM design support document, Rev. 1.2”
- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce $< 0.8 \text{ V}$ ($@V_{CC} = 3.3 \text{ V}$, $T_a = 25^\circ\text{C}$)
- Typical V_{OH} undershoot $> 2.0 \text{ V}$ ($@V_{CC} = 3.3 \text{ V}$, $T_a = 25^\circ\text{C}$)
- High output current $\pm 24 \text{ mA}$ ($@V_{CC} = 3.0 \text{ V}$)

Function Table

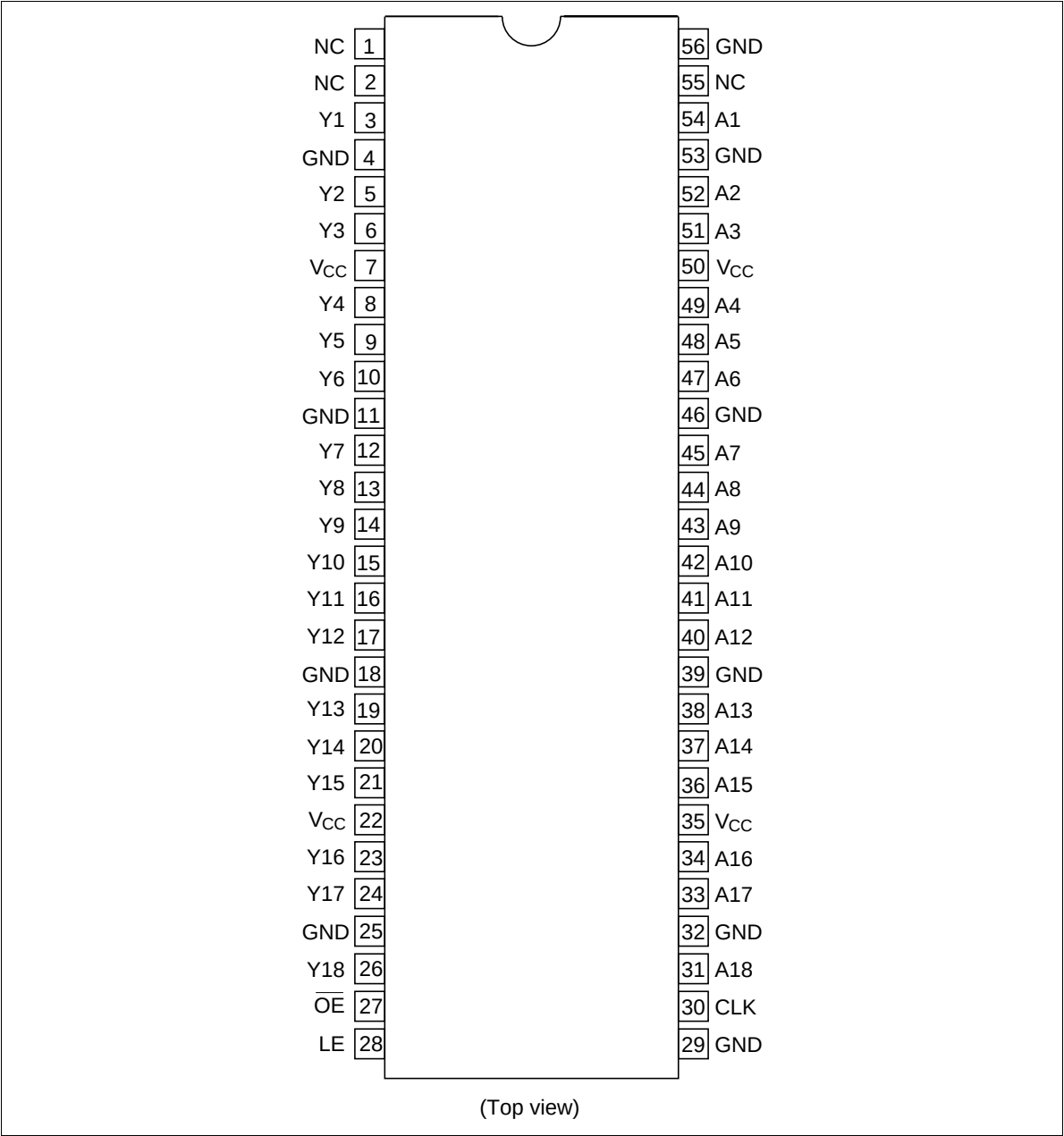
Inputs

OE	LE	CLK	A	Output Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	Y ₀ ^{*1}
L	L	L	X	Y ₀ ^{*2}

- H : High level
L : Low level
X : Immaterial
Z : High impedance
↑ : Low to high transition

Notes: 1. Output level before the indicated steady-state input conditions were established, provided that CLK was high before LE went low.
2. Output level before the indicated steady-state input conditions were established.

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V_{CC}	−0.5 to 4.6	V	
Input voltage range ^{*1}	V_I	−0.5 to 4.6	V	
Output voltage range ^{*1, 2}	V_O	−0.5 to $V_{CC}+0.5$	V	
Input clamp current	I_{IK}	−50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	$V_O = 0$ to V_{CC}
V_{CC} , GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at $T_a = 55^{\circ}\text{C}$ (in still air) ^{*3}	P_T	1	W	TSSOP
Storage temperature range	T_{stg}	−65 to 150	$^{\circ}\text{C}$	

Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating condition” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- Notes: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp current ratings are observed.
2. The input and output positive-voltage ratings may be exceeded up to 4.6 V if the input and output clamp-current ratings are observed.
3. The maximum power dissipation is calculated using a junction temperature of 150°C and board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V_{CC}	2.3	3.6	V	
Input voltage	V_I	0	V_{CC}	V	
Output voltage	V_O	0	V_{CC}	V	
High-level output current	I_{OH}	—	−12	mA	$V_{CC} = 2.3\text{ V}$
		—	−12		$V_{CC} = 2.7\text{ V}$
		—	−24		$V_{CC} = 3.0\text{ V}$
Low-level output current	I_{OL}	—	12	mA	$V_{CC} = 2.3\text{ V}$
		—	12		$V_{CC} = 2.7\text{ V}$
		—	24		$V_{CC} = 3.0\text{ V}$
Input transition rise or fall rate	$\Delta t/\Delta v$	0	10	ns/V	
Operating free-air temperature	T_a	−40	85	$^{\circ}\text{C}$	

Note: Unused or floating control pins must be held high or low.

Electrical Characteristics

Ta = -40 to 85°C

Item	Symbol	V _{CC} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	—	V	
		2.7 to 3.6	2.0	—		
	V _{IL}	2.3 to 2.7	—	0.7	V	
		2.7 to 3.6	—	0.8		
Output voltage	V _{OH}	2.3 to 3.6	V _{CC} -0.2	—	V	I _{OH} = -100 μA
		2.3	2.0	—		I _{OH} = -6 mA, V _{IH} = 1.7 V
		2.3	1.7	—		I _{OH} = -12 mA, V _{IH} = 1.7 V
		2.7	2.2	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.4	—		I _{OH} = -12 mA, V _{IH} = 2.0 V
		3.0	2.0	—		I _{OH} = -24 mA, V _{IH} = 2.0 V
	V _{OL}	2.3 to 3.6	—	0.2	V	I _{OL} = 100 μA
		2.3	—	0.4		I _{OL} = 6 mA, V _{IL} = 0.7 V
		2.3	—	0.7		I _{OL} = 12 mA, V _{IL} = 0.7 V
		2.7	—	0.4		I _{OL} = 12 mA, V _{IL} = 0.8 V
		3.0	—	0.55		I _{OL} = 24 mA, V _{IL} = 0.8 V
Input current	I _{IN}	3.6	—	±5.0	μA	V _{IN} = V _{CC} or GND
Off state output current	I _{OZ}	3.6	—	±10	μA	V _{OUT} = V _{CC} or GND
Quiescent supply current	I _{CC}	3.6	—	40	μA	V _{IN} = V _{CC} or GND
	ΔI _{CC}	3.0 to 3.6	—	750	μA	One input at (V _{CC} -0.6)V, other inputs at V _{CC} or GND

Switching Characteristics (Ta = -40 to 85°C)

Item	Symbol	V _{cc} (V)	Min	Typ	Max	Unit	From (Input)	To (Output)		
Maximum clock frequency	f _{max}	2.5±0.2	150	—	—	MHz				
		2.7	150	—	—					
		3.3±0.3	150	—	—					
Propagation delay time	t _{PLH}	2.5±0.2	1.0	—	4.2	ns	A	Y		
		2.7	—	—	4.2					
		3.3±0.3	1.0	—	3.6					
	t _{PHL}	2.5±0.2	1.3	—	5.0		LE	Y		
		2.7	—	—	4.9					
		3.3±0.3	1.3	—	4.2					
		2.5±0.2	1.4	—	5.5		CLK	Y		
		2.7	—	—	5.2					
		3.3±0.3	1.4	—	4.5					
Output enable time	t _{ZH}	2.5±0.2	1.4	—	5.5	ns	$\overline{OE}$	Y		
		2.7	—	—	5.6					
		3.3±0.3	1.1	—	4.6					
Output disable time	t _{HZ}	2.5±0.2	1.0	—	4.5	ns	$\overline{OE}$	Y		
		2.7	—	—	4.3					
		3.3±0.3	1.3	—	3.9					
Input capacitance	C _{IN}	3.3	3.0	4.5	7.0	pF	Control inputs			
		3.3	3.0	6.0	9.0		Data inputs			
Output capacitance	C _O	3.3	3.0	7.0	9.0	pF	Y ports			

Switching Characteristics (Ta = -40 to 85°C) (cont)

Item	Symbol	V _{CC} (V)	Min	Typ	Max	Unit	From (Input)
Setup time	t _{su}	2.5±0.2	2.2	—	—	ns	Data before CLK↑
		2.7	2.1	—	—		
		3.3±0.3	1.7	—	—		
		2.5±0.2	1.9	—	—		Data before LE↓
		2.7	1.6	—	—		CLK "H"
		3.3±0.3	1.5	—	—		
		2.5±0.2	1.3	—	—		Data before LE↓
		2.7	1.1	—	—		CLK "L"
Hold time	t _h	2.5±0.2	0.6	—	—	ns	Data after CLK↑
		2.7	0.6	—	—		
		3.3±0.3	0.7	—	—		
		2.5±0.2	1.4	—	—		Data after LE↓
		2.7	1.7	—	—		CLK "H" or "L"
		3.3±0.3	1.4	—	—		
Pulse width	t _w	2.5±0.2	3.3	—	—	ns	LE "H"
		2.7	3.3	—	—		
		3.3±0.3	3.3	—	—		
		2.5±0.2	3.3	—	—		CLK "H" or "L"
		2.7	3.3	—	—		
		3.3±0.3	3.3	—	—		

Switching Characteristics (Ta = 0 to 85°C)

Item	Symbol	V _{CC} (V)	Min	Typ	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	C _L =0pF ^{*1} t _{PLH} , t _{PHL}	3.3±0.165	0.9	—	2.0	ns	A	Y
	C _L =50pF	3.3±0.165	1.0	—	4.5			
	C _L =0pF ^{*1}	3.3±0.165	1.5	—	3.0		CLK	Y
	C _L =50pF	3.3±0.165	1.7	—	4.5			
	C _L =50pF t _{SSO} ^{*1,2}	3.3±0.165	1.7	—	4.8		CLK, A	Y
Output rise / fall time	C _L =50pF t _{TLH} ^{*1} , t _{THL}	3.3±0.165	1.0	—	2.5	volts/ ns		Y

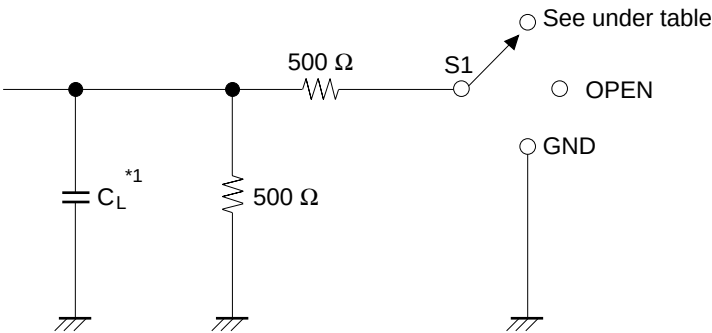
Notes: 1. This parameter is characterized but not tested.

2. t_{SSO} : Simultaneous switching output time.

Operating Characteristics (Ta = 25°C)

Item	Symbol	V _{CC} = 2.5±0.2 V	V _{CC} = 3.3±0.3 V	Unit	Test Conditions
Power dissipation capacitance	Outputs enable	22.0	24.5	pF	C _L = 0, f = 10 MHz
	Outputs disable	5.0	6.0		

Test Circuit

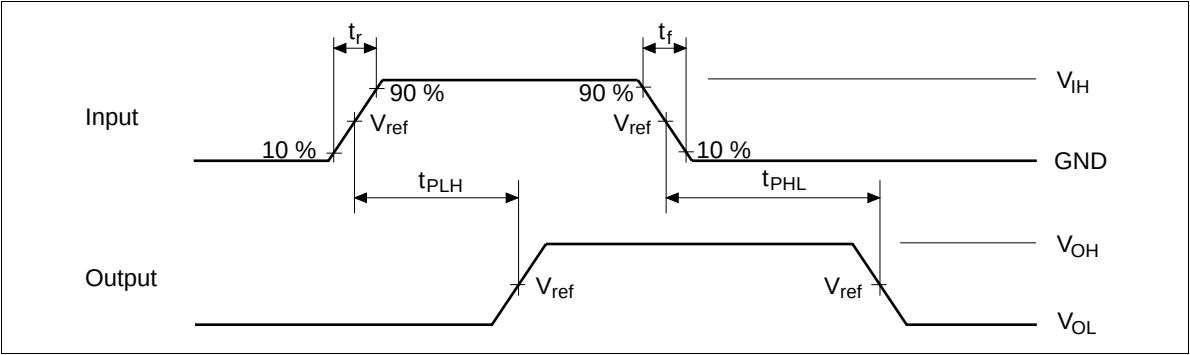


Load Circuit for Outputs

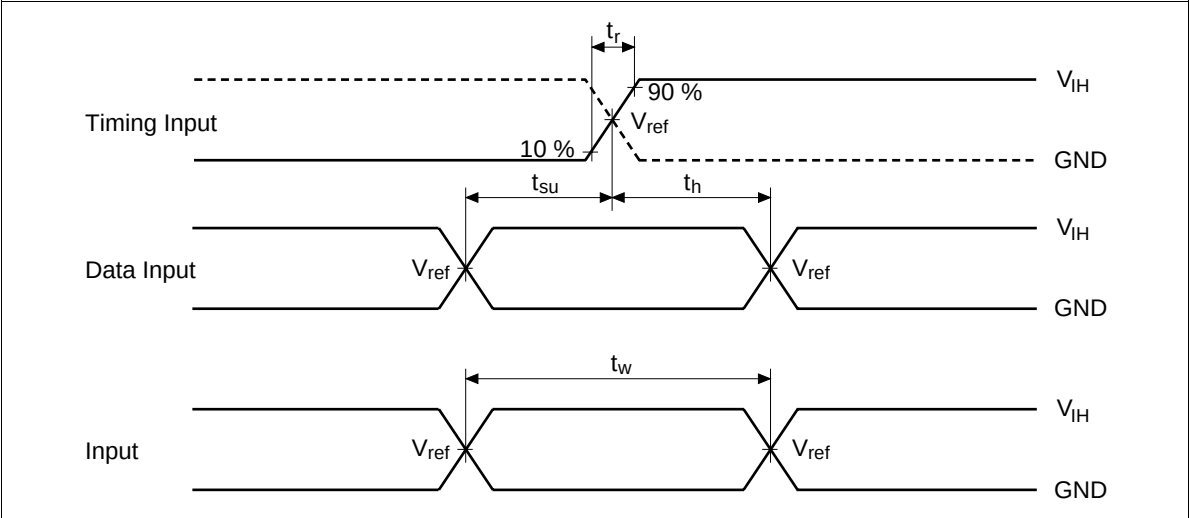
Symbol	V _{CC} =2.5±0.2V	V _{CC} =2.7V, 3.3±0.3V
t _{PLH} /t _{PHL}	OPEN	OPEN
t _{su} /t _h /t _w	OPEN	OPEN
t _{ZH} /t _{HZ}	GND	GND
t _{ZL} /t _{LZ}	2 × V _{CC}	6.0 V
C _L	30 pF	50 pF

Note: 1. C_L includes probe and jig capacitance.

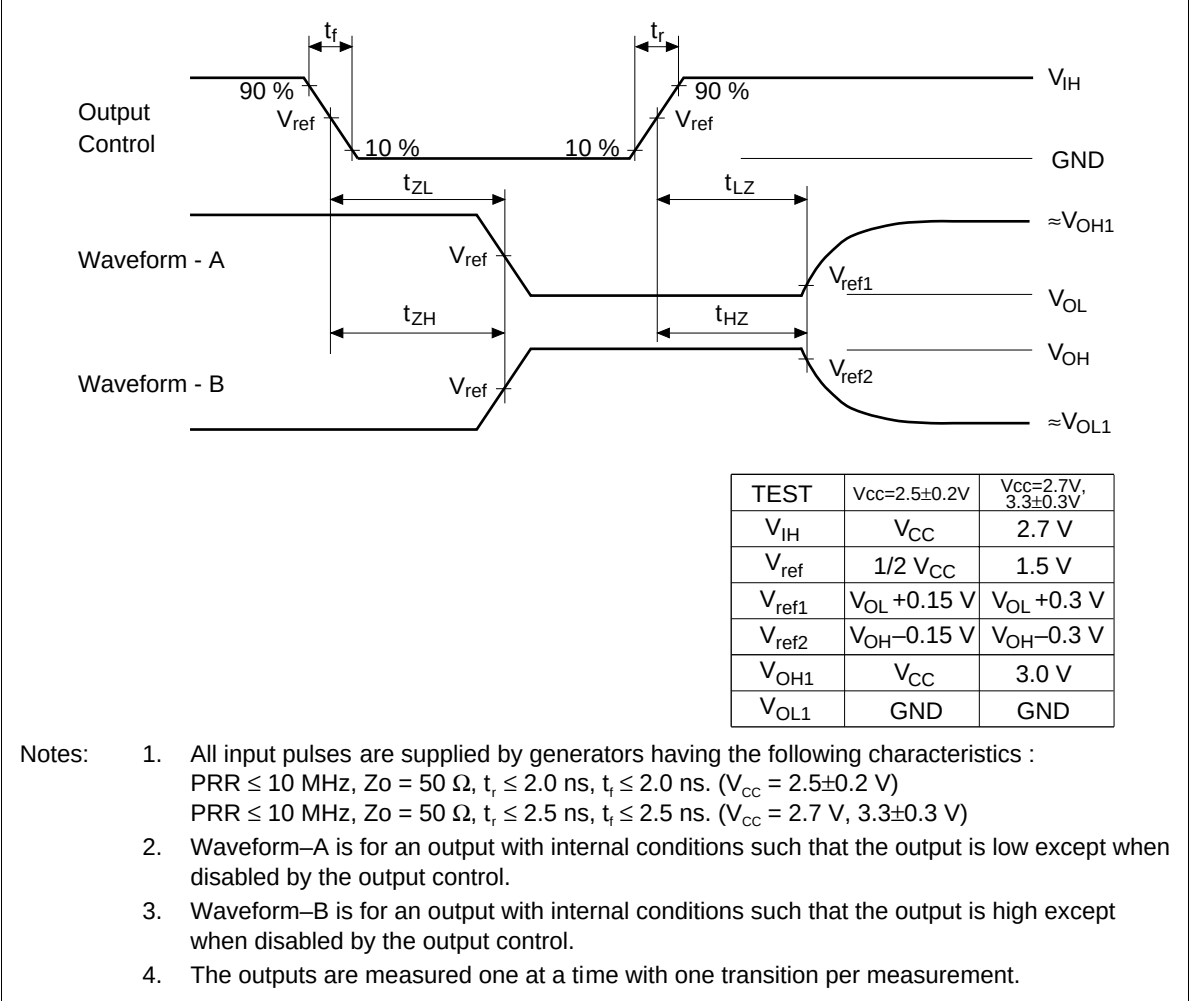
Waveforms – 1



Waveforms – 2

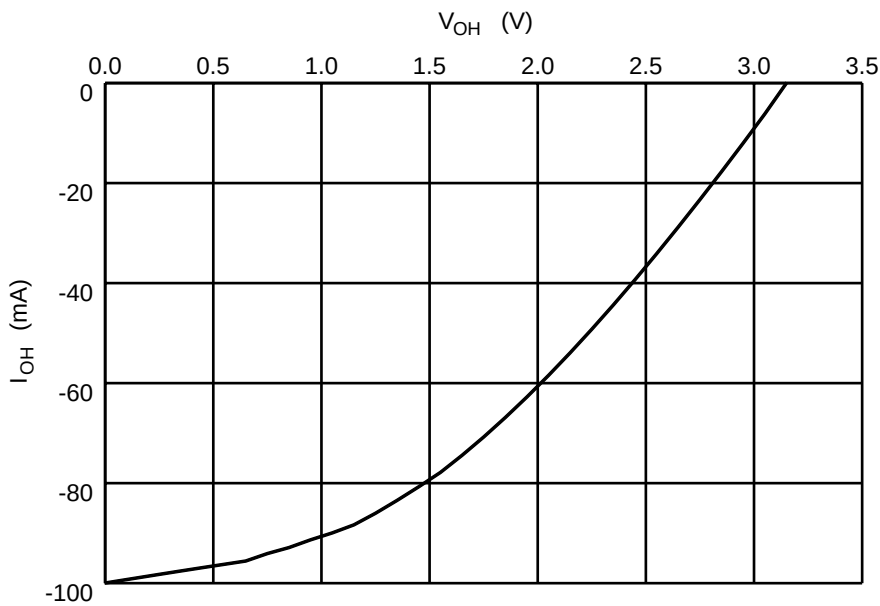


Waveforms – 3

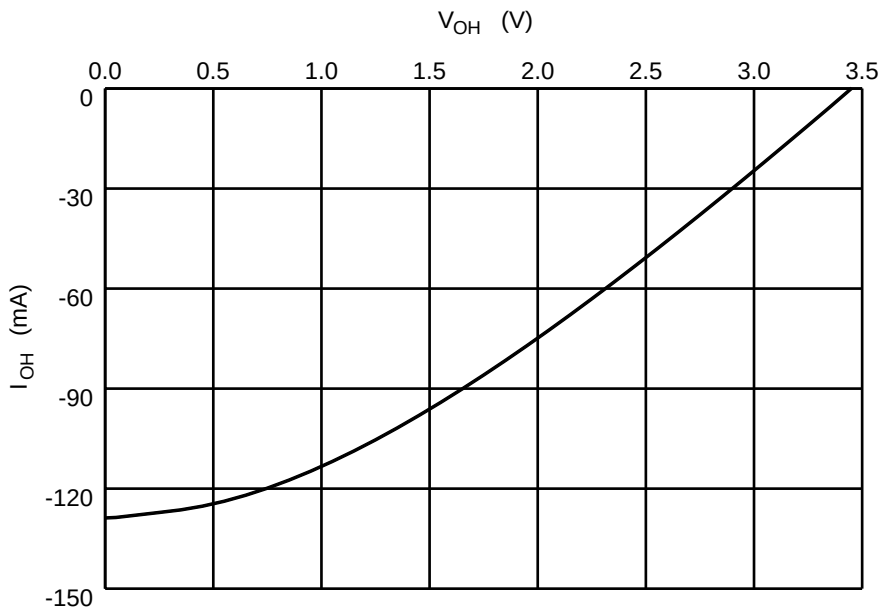


IV Characteristics for Register Output (Measured value)

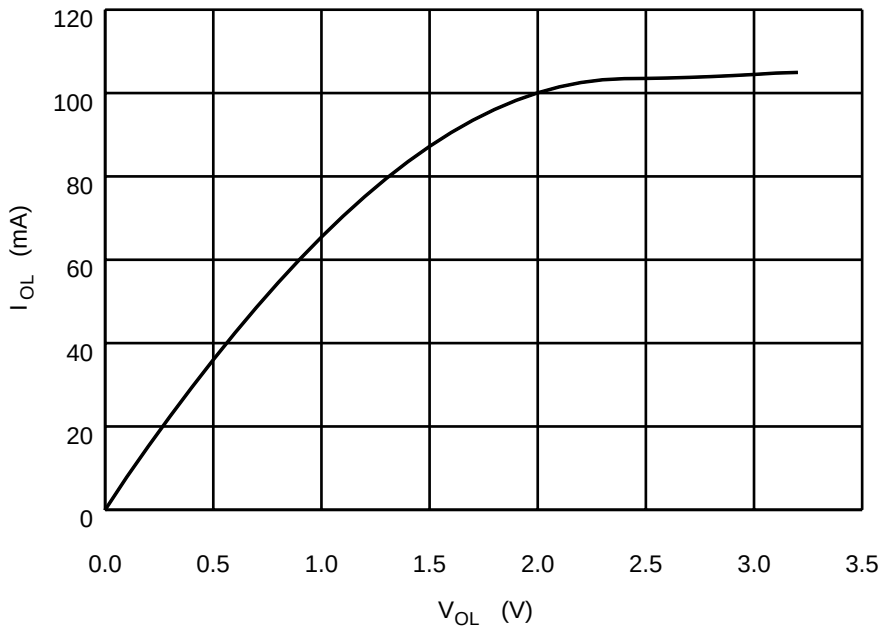
Weak condition HIGH
Vcc = 3.15 V, Ta = 85°C



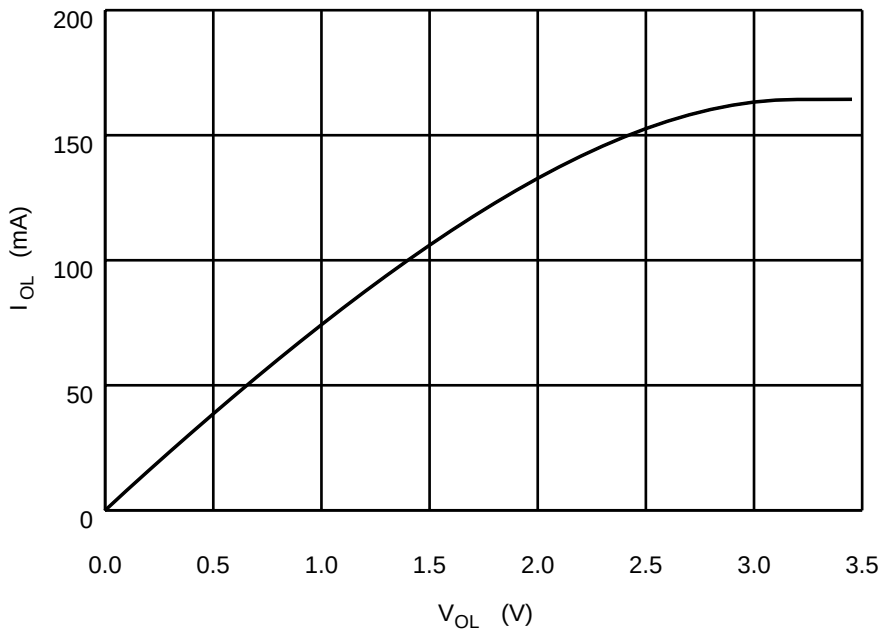
Strong condition HIGH
Vcc = 3.45 V, Ta = 0°C



Weak condition LOW
Vcc = 3.15 V, Ta = 85°C

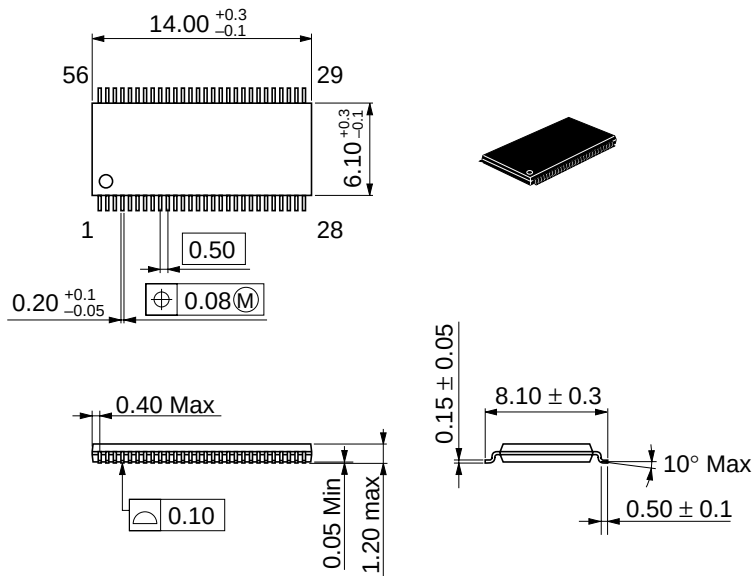


Strong condition LOW
Vcc = 3.45 V, Ta = 0°C



Package Dimensions

Unit : mm



Hitachi code	TTP-56D
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